

#### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> Max	Package	I <sub>D</sub> T <sub>A</sub> = +25°C
-20V	$52m\Omega @V_{GS} = -4.5V$	SOT23	-5.0A
-200	100mΩ @V <sub>GS</sub> = -2.5V	30123	-3.6A

### **Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters
- Motor Control

### **Features**

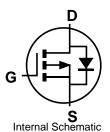
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability
- PPAP Capable (Note 4)

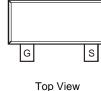
### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (4)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)









D

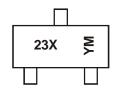
## Ordering Information (Note 5)

Part Number	Compliance	Case	Packaging
DMG2305UXQ-7	Automotive	SOT23	3,000/Tape & Reel
DMG2305UXQ-13	Automotive	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product compliance definitions.html
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



23X = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key

Year	2009	9	~		2016	20	17	2018		2019	2	2020
Code	W		~		D		E	F		G		Н
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage	$V_{DSS}$	-20	V		
Gate-Source Voltage		$V_{GSS}$	±8	V	
Continuous Dusin Comment (Nets C) // 4 5/4	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	l <sub>D</sub>	-4.2 -3.3	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = -4.5V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-5.0 -4.0	А
Pulsed Drain Current (Note 7)		I <sub>DM</sub>	-10	Α	

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit	
Power Dissipation (Note 6)		$P_{D}$	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)  Steady State t<10s		R <sub>θJA</sub>	90 64	°C/W
Thermal Resistance, Junction to Case (Note 8)	Rejc	33	°C/W	
Operating and Storage Temperature Range		$T_{J_{i}}T_{STG}$	-55 to +150	°C

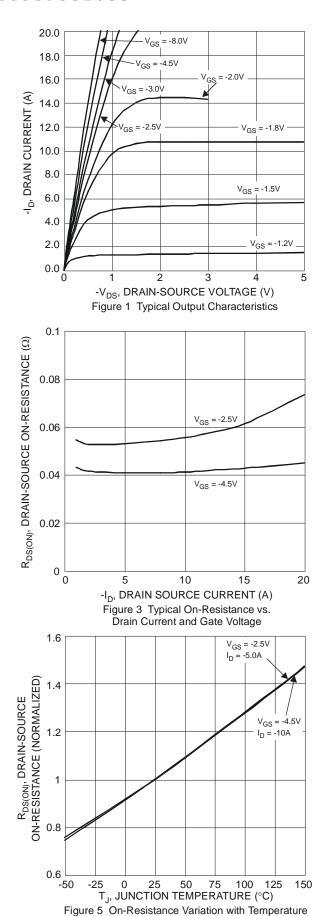
## **Electrical Characteristics** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

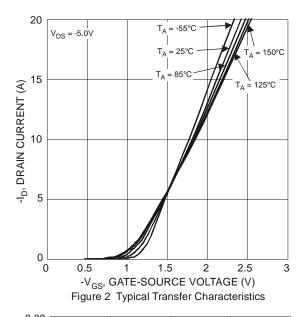
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20		_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current (T <sub>J</sub> = +25°C)	I <sub>DSS</sub>	_		-1.0	μΑ	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_		±100	nA	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.5	_	-0.9	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			40	52		$V_{GS} = -4.5V$ , $I_D = -4.2A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	52	100	mΩ	$V_{GS} = -2.5V, I_D = -3.4A$	
			68	200		$V_{GS} = -1.8V, I_D = -2A$	
Forward Transfer Admittance	Y <sub>FS</sub>	_	9	_	S	$V_{DS} = -5V, I_{D} = -4A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>ISS</sub>	_	808	—	pF	V 45V V 0V	
Output Capacitance	Coss	_	85	_	pF	$V_{DS} = -15V, V_{GS} = 0V$ - f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	77	_	pF	1 = 1.01/11 12	
Gate Resistance	$R_{G}$		15.2		Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$	
SWITCHING CHARACTERISTICS (Note 9)							
Total Gate Charge	$Q_G$	_	10.2	_	nC	\/ 4.5\/\/ 4\/	
Gate-Source Charge	$Q_GS$	_	1.3		nC	$V_{GS} = -4.5V, V_{DS} = -4V,$ $I_{D} = -3.5A$	
Gate-Drain Charge	$Q_GD$	_	2.2	_	nC	ID = -3.5A	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	10.8	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	13.7	_	ns	$V_{DS} = -4V$ , $V_{GS} = -4.5V$ ,	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	79.3	_	ns	$R_G = 6\Omega$ , $I_D = -1A$	
Turn-Off Fall Time	t <sub>F</sub>	_	34.7	_	ns		

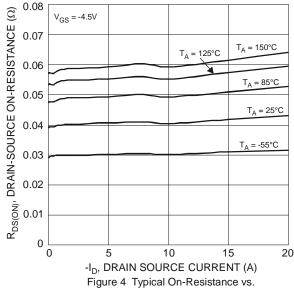
Notes:

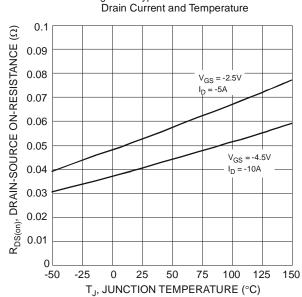
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
   Repetitive rating, pulse width limited by junction temperature.
   Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing













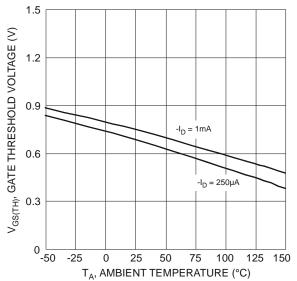
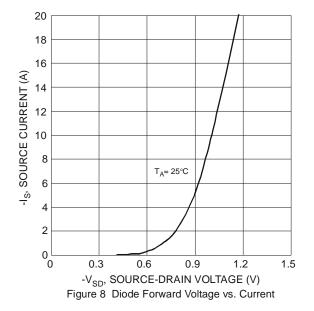


Figure 7 Gate Threshold Variation vs. Ambient Temperature

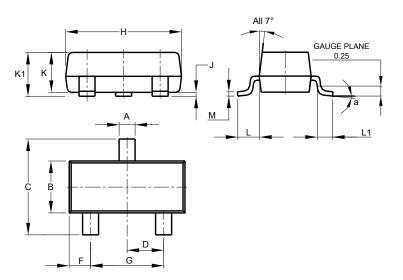




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23

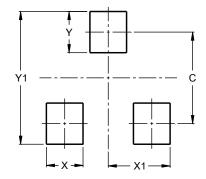


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All	All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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